

WHAT IS CLAIMED IS:

1. A plasma processing apparatus provided with a holding stage of a system in which a temperature of an electrode block is controlled so as to control a temperature of a semiconductor wafer, wherein said electrode block is provided with at least first and second independent temperature control means on the inner and outer sides thereof and, a slit for suppressing heat transfer is provided in said electrode block between said first and second independent temperature control means.
2. A plasma processing apparatus according to claim 1, wherein said slit for suppressing heat transfer is formed substantially concentrically.
3. A plasma processing apparatus according to claim 1, wherein a heater is provided on the backside of said electrode block.
4. A plasma processing apparatus according to claim 1, wherein a heater is built in said electrode block.
5. A plasma processing apparatus according to claim 1, wherein said electrode block is provided, on the surface thereof, with a dielectric film.
6. A plasma processing apparatus according to claim 1, wherein said electrode block is provided with temperature sensors and temperature control is performed on the basis of information from said temperature sensors.